

L-Band, GaN/SiC, RF Power Transistor

1030 and 1090 MHz | 450 W typ | 65% Efficiency typ | 17.5 dB Gain typ | 50 V | 128μs Pulse Length, 2% Duty Cycle

IGN1011M400 and IGN1011M400S are high power GaN-on-SiC RF power transistors that have been designed to suit the unique needs of IFF/SSR avionics systems. They operate at 1030 and 1090 MHz. Under 128 μ s, 2% duty-cycle pulse conditions, they supply a minimum of 400 W of peak output power, with typically 16dB of associated gain and 65% efficiency. They operate from a 50 V supply voltage. For optimal thermal efficiency, the transistors are housed in a metal-based package with an epoxy-sealed ceramic lid.



FEATURES

- GaN on SiC HEMT Technology
- Output Power >400 W
- Pre-matched Input Impedance
- High Efficiency up to 70%
- 100% RF Tested Under 128μs, 2% duty-cycle pulse conditions
- RoHS and REACH Compliant

APPLICATIONS

- L-band Avionics IFF & SSR Systems
- Suitable for both uplink and downlink (Transponder)

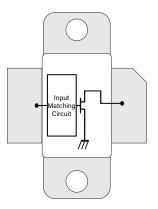


Table 1. RF Electrical Characteristics (Case temperature = 30 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
RF Input Power	P _{IN, RF}	8	10	12.5	W	P _{out} =400W
Gain	G	15	16	17	dB	f = 1030, 1090 MHz
Drain Efficiency	η	50	65	75	%	128µs, 2% duty-cycle pulse conditions
Pulse Droop	D	-0.4	-0.25	+0.2	dB	
Input Return Loss	IRL	10	14	18	dB	$V_{DS} = 50V, I_{DS} = 90mA$
Load Mismatch Stability	VSWR-S	2:1				
VSWR Withstand	VSWR-LMT	3:1				

Note: Consult Integra Technologies Application Note 001 for information on how RF output power and pulse droop are measured.



Table 2. Absolute Maximum Ratings (Not Simultaneous)

Parameter	Symbol	Value	Units	Test Conditions
DC Drain-Source Voltage	$V_{\scriptscriptstyle DS}$	150	V	25 °C
DC Gate-Source Voltage	V _{GS}	-8 to +1.0	V	25 °C
DC Drain Current	I _D	36	A	25 °C
DC Gate Current	I _G	36	mA	25 °C
RF Input Power	P _{REIN}	18	W	25 °C
Operating Channel Temperature	Т _{сн}	-55 to +225	°C	
Storage Temperature	T _{stg}	-55 to +150	°C	
Soldering Temperature	T _{SOLDER}	260 for 60s	°C	

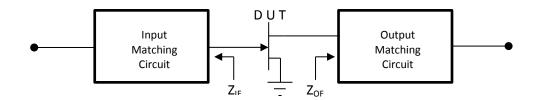
Note: Operation outside the limits given in this table may cause permanent damage to the transistor

Table 3. DC Electrical Characteristics (Case temperature = 25 °C unless otherwise stated)

Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
Gate Pinch-Off Voltage	V _P	-5.0			V	$V_{DS} = 50V$, $I_{DS} = 1mA$
Quiescent Gate Voltage	V _Q		-2.8		V	V _{DS} = 50V, I _{DS} = 90mA

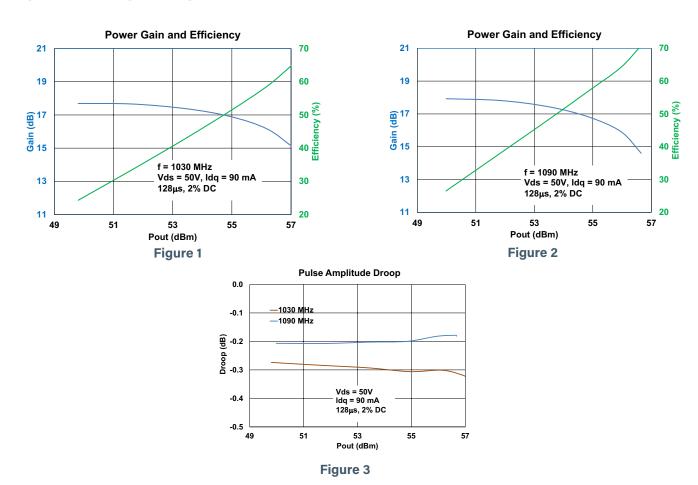
Table 4. Test Fixture Source & Load Impedances (Case temperature = 25 °C unless otherwise stated)

Frequency (MHz)	Z _{IF}	Z _{of}	Units	Test Conditions
1030	4.2 - j 1.9	2.1 - j 1.0	Ω	P _{OUT} = 400W 128μs, 2% duty-cycle pulse conditions
1090	4.2 - j 0.9	2.1 - j 0.2	Ω	$V_{DS} = 50V$, $I_{DQ} = 90$ mA





TYPICAL RF PERFORMANCE

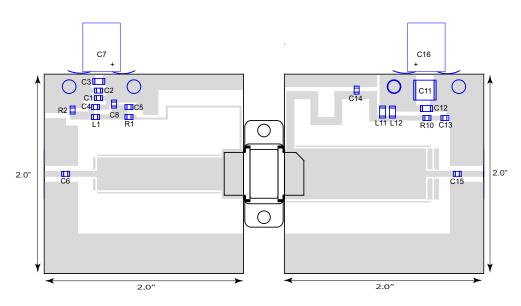


TYPICAL THERMAL PERFORMANCE

Peak Thermal Resistance, Channel to Case $R_{TH} = 0.32$ $^{\circ}$ $C/W = 0.32$ $^{\circ}$	Parameter	Symbol	Min	Тур	Max	Units	Test Conditions
1.4 1.2 1.0 0.6 0.4 0.2 0.0		R _{TH}		0.32		°C/W	128µs, 2% duty-cycle pulse conditions
$\begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \\ \\ \\ \\ \end{array} \end{array} \begin{array}{c} \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \end{array} \begin{array}{c} \\ \\$			1.4				
0.4 0.2 0.0 P _{Diss} = 215W T _{Flange} = + 85°C		tth (°C/W	0.8				T _{ch} = 225 °C
0.0			0.4				P _{Diss} = 215W T _{Flange} = + 85°C
			0.0	1.E-07	1.E-05	1.E-03	1.E-01 1.E+01



TEST FIXTURE



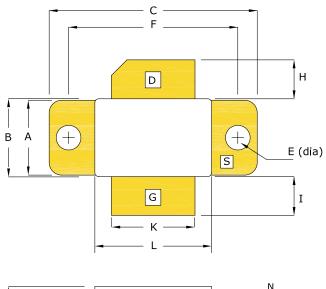
Note: Energy storage capacitors C7 and C16 are mounted external to the PCB between the drain and ground terminals and between the gate and ground terminals. It is recommended that they be placed as close as possible to the test fixture in order to minimise pulse droop.

Bill of Materials for IGN1011M400 Test Fixture

Designator	Description	Part Number
C1, C4, C13	CAP 0.1µF, 0805, 50V, X7R	08051C104K4T2A
C2, C5, C6, C14, C15	CAP 33pF, 0805	ATC600F330
C3, C12	CAP 1µF, 1206, 100V, X7R	12061C105K4T2A
C7, C16	CAP 68μF, 63V, Electrolytic	UPW1J680MPD
C8	CAP 1000pF, 0805, 100V	08051A102J4T2A
L1	IND, FB, 120 OHM, 0805, 5A	ILHB0805ER121V
L11, L12	IND , FB, 33 OHM, 1206, 6A	BLM31PG330SN1L
R1, R10	RES, 15 OHM, 0805	ERJ-6ENF150V
R2	RES, 100 OHM, 0805	ERJ-6ENF2000V
PC Board Type	ROGERS RO4350B, 30mil, 1/1oz. Copper	



PACKAGE PL64A1

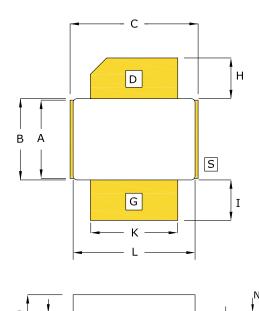


	INCHES	2	MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.380	0.390		
В	0.395	0.405		
С	1.065	1.075	27.05	27.31
E	0.124	0.130	3.15	3.30
F	0.865	0.875	21.97	22.23
Н	0.190	0.223	4.83	5.66
I	0.190	0.223	4.83	5.66
J				
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
М	0.060	0.070	1.52	1.78
N	0.004	0.006	0.10	0.15
	0.096	0.106	2.44	2.69
Р	0.181	0.214	4.60	5.44

PIN SCHEDULE		
D	DRAIN	
S	SOURCE	
G	GATE	



BOLT-DOWN FLANGE OPTION IGN1011M400



	INCHES	3	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.380	0.390	9.65	9.91
В	0.395	0.405	10.03	10.29
С	0.625	0.635	15.88	16.13
E				
F				
Н	0.190	0.223	4.83	5.66
I	0.190	0.223	4.83	5.66
J				
K	0.425	0.435	10.80	11.05
L	0.595	0.605	15.11	15.37
М	0.060	0.070	1.52	1.78
N	0.004	0.006	0.10	0.15
	0.096	0.106	2.44	2.69
Р	0.181	0.214	4.60	5.44

PIN	SCHEDULE
D	DRAIN
S	SOURCE
G	GATE

EARLESS FLANGE OPTION IGN1011M400S



ESD & MSL Rating

Parameter	Rating	Standard
ESD Human Body Model (HBM)	TBD	ESDA/JEDEC JS-001-2012
ESD Charged Device Model (CDM)	TBD	JEDEC JESD22-C101F
Moisture Sensitivty Level (MSL)	Unlimited Shelf Life	IPC/JEDEC J-STD-020

RoHS Compliance

Integra Technologies, Inc declares that its GaN and LDMOS Transistor Products comply with EU Directive 2011/65/EU on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863/EU.

REACH Compliance

Integra Technologies supports EU Regulation number 1907/2006 concerning the Registration, Evaluation, Authorization, and Restriction of Chemicals (REACH) as these apply to Integra semiconductor products, development tools, and shipping packaging.

In support of the REACH regulation, Integra will:

- Inform customers and recipients of Integra product if they contain any substances that are of very high concern (SVHC) per the European Chemical Agency (ECHA) website.
- Notify ECHA if any Integra product that contains any SVHCs which exceed guidelines for REACH chemicals by weight per part number and for total content weight per year for all products produced in or imported to the European market.
- •Cease shipments of product containing REACH Annex XIV substances until authorization has been obtained.
- Cease shipment of product containing REACH Annex XVII chemicals when restrictions apply.

Integra has evaluated its materials, BOMs, and product specifications and product and has determined that this transistor conforms to all REACH and SVHC regulations and guidelines. Integra has implemented actions and control programs that will assure continued compliance.

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DATA SHEET STATUS

Advanced Specification - This data sheet contains Advanced specifications.

Preliminary Specification - This data sheet contains specifications based on preliminary measurements and data.

Final Specification - This data sheet contains final product specifications.

MAXIMUM RATINGS Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.Integra Technologies, 321 Coral Circle, El Segundo, CA 90245-4620 | Phone: 310-606-0855 | Fax: 310-606-0865